



MoTiC: Prototype of a Monolithic Particle Tracking Detector with Timing

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Motivation

- The PSI High Energy Physics group in collaboration with ETHZ has a generic R&D program for DMAPS since 2019
- Several technologies are being evaluated
- Goal: radiation hard detectors featuring timing
- Aiming for
 - Spatial resolution of O(10 μm)
 - Sub-nanosecond timing resolution



Depleted Monolithic Active Pixel Sensors (DMAPS)



- Left: Hybrid pixel detector (such as the current pixel detector at CMS): More complex, but each piece of silicon can be optimized for its purpose.
- Right: DMAPS: All components are processed on the same wafer.



MoTiC: Monolithic Timing Chip



- Manufactured in a modified 110 nm CMOS process
- Pixel pitch: 50 x 50 μm²
- 80 columns by 64 rows (5120 pixels)
- Full frame readout
- In-pixel discriminators and TDC shared by 4 pixels
- 7 pixel flavours with different preamplifier designs
- Sister chip with varying sensor geometries and test structures (MoTiC B)



Process Overview: Modified LFoundry 110 nm Process

N-type substrate wafers



- All sensing structures designed by ARCADIA
- Small electrodes with small capacitance
- The wafers are backside processed to have guard rings and backside metal contact.
- Depletion from the backside
- Active thicknesses of 50, 100, 200 μm

The development of the process modification and sensor nodes has been performed in the framework of the INFN CSN5 Call ARCADIA. Image Source: [1]



Pixel Schematic





Time to Digital Converter (TDC)



- Start signal: Hit, stop signal: clock or reference signal
- Ring oscillator, adjustable frequency of O(500 MHz to 1 GHz)
- Coarse resolution (O(ns)): number of revolutions counted
- Sub-nanosecond resolution: charging a capacitor to measure time to finish last revolution (analog readout)



Time to Digital Converter (TDC)



- · Left: 2 standalone TDCs, analog response vs. external delay
- Right: residuals of TDCs
- O(10 ps) TDC resolution achieved
- Flat top removed in next submission



DAQ System



- Regulators for chip power supply
- Two high speed ADCs for pulse heights and TDC ramp
- Two FPGAs
 - Max10 for direct communication with the chip
 - Enclustra SoC (Cyclone V) for readout control
- 48 DAC/ADC channels
- Delay chip to test TDC
- Dedicated DAQ soft- and firmware with integration in EUDAQ2



Calibration Pulses



- Basic functionality verified in the lab
- Left and Middle: Inject calibration pulses in pattern resulting pulse height and hit map
- Right: Pulse forms of varying injection charges



Leakage of Sample & Hold Capacitor



- Read out all pixels sequentially
- Pulse height pedestal as a function of pixel index
- Sample & Hold capacitor (MOSCap) very leaky
- All charge leaking away within \sim 1 ms
- Steps due to variation in the end-of-column amplifiers
- This and other issues fixed in v2 tapeout in June 2022 (received a few weeks ago)



Test Beam at DESY



- Took place Nov 21 Nov 28 2022
- 4-5 GeV/c electrons
- 6 Alpide planes
- $\sim 28 \ x \ 28 \ \mu m^2$ pixels
- Tracking resolution $\lesssim 5 \ \mu m$
- Coincidence of scintillators as trigger





Efficiency Map



- Efficiency across full matrix.
- Red borders show different preamplifier designs.
- Top right flavour has a larger feedback capacitance leading to a lower gain.



Spatial Resolution at Vertical Incidence



- Resolution: RMS of the distance to the reconstructed track.
- Better than binary resolution (\sim 14.4 μ m)
- This is due to significant charge sharing even at vertical incidence.
- Best resolution of 6.5 μm achieved at an incident angle of 10°.



Charge Map of Associated Clusters

Charge map for associated clusters



- Only right half of the chip is read out.
- Different preamplifier flavours are visible.
- Top right flavour has a larger feedback capacitance.



Charge Distribution of Associated Clusters



- Charge distribution of associated clusters.
- Samples of 50, 100, 200 µm active thickness.
- MPV of roughly 500, 1000, 2000 ADC counts.
- MPV proportional to active thickness.
- 1 ADC count \approx 8 e⁻.



Summary and Outlook



- A new prototype DMAPS chip has been designed in a modified LFoundry 110 nm process.
- High efficiency (99.7 %) and good spatial resolution (6.5-8 μm) measured in test beam
- More analysis on the different preamplifier flavours to be performed
- In-pixel TDC to be tested
- MoTiCv2 received end of April 2023. Leakage is fixed, but other new problems to be understood



References

- L. Pancheri et al., "Fully Depleted MAPS in 110-nm CMOS Process With 100-300 um Active Substrate," IEEE Transactions on Electron Devices, vol. 67, no. 6, pp. 2393–2399, 2020.
- [2] L. Pancheri et al., "A 110 nm CMOS process for fully-depleted pixel sensors," *Journal of Instrumentation*, vol. 14, pp. C06016–C06016, jun 2019.
- [3] C. Neubüser et al., "Sensor design optimization of innovative low-power, large area fd-maps for hep and applied science," *Frontiers in Physics*, vol. 9, 2021.
- [4] R. Diener et al., "The DESY II test beam facility," Nuclear Instruments and Methods in Physics Research Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, vol. 922, pp. 265–286, 2019.
- [5] D. Dannheim et al., "Corryvreckan: a modular 4d track reconstruction and analysis software for test beam data," *Journal of Instrumentation*, vol. 16, p. P03008, mar 2021.



Spatial Resolution



- Particles inducing charge in multiple pixels form clusters (charge sharing).
- Exact hit position is calculated by the center-of-gravity of the pulse heights.
- Resolution: RMS of the distance to the reconstructed track.
- Significantly better than binary resolution (\sim 14.4 $\mu m)$ even at vertical incidence.
- Optimal charge sharing angle for 200 μm at 10°.



MoTiC B: Sister Chip with Test Structures



- 4 different sensor geometries designed by ARCADIA
- 1 AC coupled pixel
- Test structures for (edge) TCT measurements



Readout Mode in Test Beam



- An external trigger starts the readout sequence with a delay of \sim 200 ns.
- The Sample & Hold circuit is set on hold to store pulse heights on the capacitors.
- All pixels are read out sequentially with shift registers.
- No buffers or digitization on chip, this is handled on the DAQ board.
- Discriminator and TDC not used at present.
- For hit discrimination an offline threshold of 8 times the noise (σ of the pedestal) is used.



N-pixel cluster Maps





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Process Overview: Modified LFoundry 110 nm process (2)

P-type substrate wafers



- All sensing structures designed by ARCADIA[1, 2, 3]
- P-substrate with 2 epitaxial n-layers
- Total thickness of epitaxial layers is 48 μm
- Physical wafer thickness is 300 μm
- Biased via conducting chip edge

The development of the process modification and sensor nodes has been performed in the framework of the INFN CSN5 Call ARCADIA. Image Source: [1]



Depleting the sensors



d / µm	Bias	V_D	<i>I_L @ V_D /</i> μΑ
200	Backside	\sim 50 V	\sim 20-30
100	Chip Edge	\sim 35 V	\sim 500-1000
48	Chip Edge	\sim 35 V	\sim 500-1000

- High leakage caused by the conductive chip edge
- Full depletion is necessary to see signals.
- Leakage current flows into top-side guard ring and not into pixels.



Preamplifier Designs





Telescope at TB24



- Very clean telescope
- Integration time of O(10 μs)
- No need for timing reference plane
- 1 track per event
- Tracking resolution $\lesssim 5~\mu m$



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Preamplifier Calibration



Preamp Calibration Sample 172 1200 - --- Preamp A - Preamp B Preamp C 1000 ---- Preamn D Preamp E Preamp F1 800 Preamp E2 Heigt / a. 600 400 200 ò 200 400 600 800 1000 1200 Veal / mV



